MPS4250

Transistor

PNP Silicon

ON Semiconductor®

http://onsemi.com

Features

- This is a Pb−Free Device*

MAXIMUM RATINGS

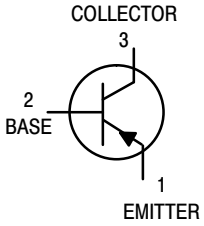
Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−40	Vdc
Collector − Emitter Voltage	V_{CES}	−40	Vdc
Collector − Base Voltage	V_{CBO}	−40	Vdc
Emitter − Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−50	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	W mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

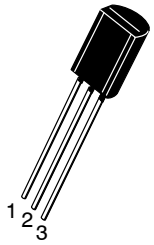
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

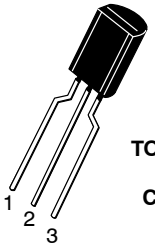
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





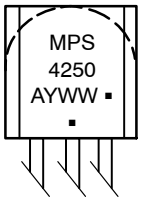
STRAIGHT LEAD
BULK PACK



BENT LEAD
TAPE & REEL
AMMO PACK

TO−92 1 WATT
(TO−226)
CASE 29−10
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MPS4250G	TO−92 (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

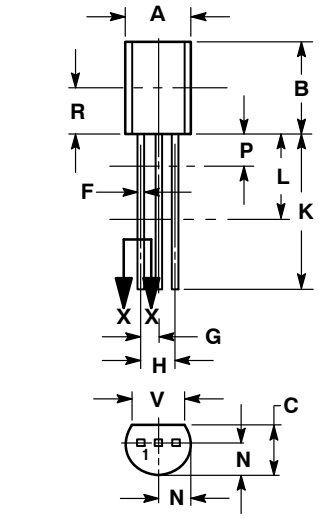
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = –5.0 mA)	$V_{(BR)CES}$	–40	–	Vdc
Collector – Emitter Sustaining Voltage (Note 1) (I_C = –5.0)	$V_{(BR)CEO(sus)}$	–40	–	Vdc
Collector – Base Breakdown Voltage (I_C = –10 μA)	$V_{(BR)CBO}$	–40	–	Vdc
Emitter – Base Breakdown Voltage (I_E = –10 μA)	$V_{(BR)EBO}$	–5.0	–	Vdc
Collector Cutoff Current (V_{CB} = –50 V) (V_{CB} = –40 V, T_A = 65°C)	I_{CBO}	 – –	 –10 –3.0	 nA μA
Emitter Cutoff Current (V_{EB} = –3.0 V)	I_{EBO}	–	–20	nA
ON CHARACTERISTICS				
DC Current Gain (I_C = –1.0 mA, V_{CE} = –5.0 V) (I_C = –10 mA, V_{CE} = –5.0 V)	h_{FE}	 250 250	 – –	–
Collector – Emitter Saturation Voltage (Note 1) (I_C = –10 mA, I_B = –0.5 mA)	$V_{CE(sat)}$	–	–0.25	Vdc
Base – Emitter Saturation Voltage (Note 1) (I_C = –10 mA, I_B = –0.5 mA)	$V_{BE(sat)}$	–	–0.9	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Output Capacitance (V_{CB} = –5.0 V, f = 1.0 MHz)	C_{obo}	–	6.0	pF
Input Capacitance (V_{EB} = –0.5 V, f = 1.0 MHz)	C_{ibo}	–	16	pF
Small–Signal Current Gain (I_C = –1.0 mA, V_{CE} = –5.0 V, f = 1.0 kHz) (I_C = –0.5 mA, V_{CE} = –5.0 V, f = 20 MHz)	h_{fe}	 250 2.0	 800 –	–
Noise Figure (I_C = –20 μA, V_{CE} = –5.0 V, R_S = 10 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz) (I_C = –250 μA, V_{CE} = –5.0 V, R_S = 1.0 kΩ, f = 1.0 kHz, P_{BW} = 150 Hz)	NF	 – –	 2.0 2.0	dB

1. Pulse Test: Pulse Width = 300 μs; Duty Cycle = 2.0%.

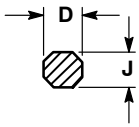
MPS4250

PACKAGE DIMENSIONS

TO−92 (TO−226) 1 WATT
CASE 29−10
ISSUE O



STRAIGHT LEAD
BULK PACK

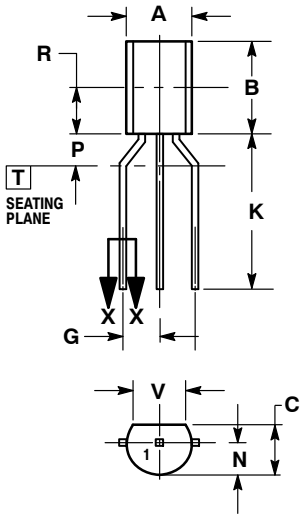


SECTION X−X

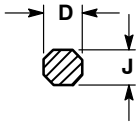
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
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DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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